

7.2 国際会議

2003 年

1. M. Matsumoto, M. Shima, S. Okamoto, K. Murata, M. Tanaka, S. Kiyama, H. Kakiuchi, K. Yasutake, K. Yoshii, K. Endo and Y. Mori: Extremely High-Rate Deposition of Silicon Thin Films Prepared by Atmospheric Plasma CVD Method with a Rotary Electrode, 3rd World Conference and Exhibition on Photovoltaic Solar Energy Conversion, Japan
2. S. Morita, A. Shinozaki, T. Okazaki, K. Nishimura, S. Urabe, and M. Morita: Control and Characterization of Ultrathin Silicon Dioxide Films, First International Symposium on Standard Materials And Metrology for Nanotechnology, Japan
3. N. Yoshii, S. Morita, A. Shinozaki, M. Aoki, and M. Morita: Energy Barrier Heights of Ultra-thin Silicon Dioxide Films with Different Metal Gates, International Workshop on Gate Insulator 2003, Japan
4. K. Arima, H. Kakiuchi, M. Ikeda, K. Endo, M. Morita and Y. Mori: Scanning tunneling microscopy observations of intrinsic hydrogenated amorphous silicon surface under visible light irradiation, 7th Int. Conference on Atomically Controlled Surfaces, Interfaces and Nanostructures, Japan
5. K. Arima, H. Kakiuchi, M. Ikeda, K. Endo, M. Morita and Y. Mori: Visible Light Irradiation Effects on Atomic-Scale Observations of Hydrogenated Amorphous Silicon Films by Scanning Tunneling Microscopy, 2003 International Conference on SOLID STATE DEVICES AND MATERIALS, Japan
6. S. Morita, A. Shinozaki, Y. Morita, K. Nishimura, T. Okazaki, S. Urabe and M. Morita: Control and Characterization of Ultrathin Silicon Dioxide Films, International Workshop on Dielectric Thin Films for Future ULSI Devices, Japan
7. Y. Oshikane, S. Sato, A. Nagao, K. Yamamura, K. Endo, Y. Mori Ultraviolet: Emission Spectroscopy and Absorption Spectroscopy of CF₂ Radical in Chemical Vaporization Machining (CVM) Plasma Generated with High Speed Rotating Cylindrical Electrode, AVS 50th International Symposium and Exhibitions, USA
8. M. Akai-Kasaya, K. Shimizu, A. Saito, M. Aono and Y. Kuwahara: Electronic Structure and Excited States of One-dimensional Polydiacetylene Nanowire, AVS 50th International Symposium & Exhibition, USA
9. A. Saito, K. Matoba, J. Maruyama, W. Yashiro, T. Ohashi, H. Takaki, K. Takami, M. Akai-Kasaya, Y. Kuwahara, Y. Yoda, O. Sakata, K. Miki, M. Aono: Characterization of Buried Nanowire by X-ray Standing Wave Method, AVS 50th International Symposium & Exhibition, USA
10. K. Takami, J. Mizuno, M. Akai-kasaya, A. Saito, M. Aono, and Y. Kuwahara: "Conductivity of the Organic Thin Films Measured by Independently-Driven Double-Tip STM", 12th International Conference on Scanning Tunneling Microscopy/Spectroscopy and Related Techniques, July 21-25, 2003 Eindhoven, Netherlands
11. A. Saito, H. Matsumoto, S. Ohnisi, M. Akai-Kasaya, Y. Kuwahara, and M. Aono: Atomic-scale Smoothing and Structural Analysis of LiNbO₃ Surface, 2003 International Conference on Solid State Devices and Materials (September, 2003 Tokyo), Japan

12. Y. Mori, K. Yamauchi, K. Yamamura, H. Mimura, Y. Sano, A. Saito, K. Endo, A. Souvorov, M. Yabashi, K. Tamasaku, T. Ishikawa: Development of a figure correction method having spatial resolution close to 0.1mm, SPIE, USA
13. Y. Mori, K. Yamauchi, K. Yamamura, H. Mimura, Y. Sano, A. Saito, K. Endo, A. Souvorov, M. Yabashi, K. Tamasaku, T. Ishikawa, M. Shimura, Y. Ishizaka: Fabrication technology of hard X-ray aspherical mirror optics and application to nanospectroscopy, SPIE, USA
14. K. Yamuchi, H. Mimura, K. Yamamura, Y. Sano, K. Ueno, S. Matsuyama, K. Endo, Y. Nishino, K. Tamasaku, M. Yabashi, T. Ishikawa: Surface figure metrology of X-ray mirror using optical interferometry at Osaka Univ and SPring-8, Second International Workshop on Metrology for X-ray Optics, France
15. Y. Mori, K. Yamuchi, K. Yamamura, H. Mimura, Y. Sano, S. Matsuyama, K. Endo, Y. Nishino, K. Tamasaku, M. Yabashi, T. Ishikawa: Fabrication technology for hard X-ray reflective optics, Second International Workshop on Metrology for X-ray Optics, France
16. T. Ono and K. Hirose: First-principles study of electron conduction through nanostructures, 6th Asian Workshop on First-Principles Electronic Structure Calculations (November 10-12, 2003 Tsukuba), Japan
17. K. Inagaki, K. Yasutake, H. Goto and K. Hirose: First-Principles Molecular-Dynamics Simulations on Extraction of Hydrogen Molecule from Hydrogen Terminated Si(001) 2x1 Surface by Hydrogen Radical, 6th Asian Workshop on First-Principles Electronic Structure Calculations (November 10-12, 2003 Tsukuba), Japan
18. H. Goto, K. Hirose, K. Inagaki and Y. Mori: First-Principles Molecular-Dynamics Simulations of Electrochemical Matching Process on Cathode Surface in Ultrapure Water, 6th Asian Workshop on First-Principles Electronic Structure Calculations (November 10-12, 2003 Tsukuba), Japan
19. M. Matsumoto, M. Shima, S. Okamoto, K. Murata, M. Tanaka, S. Kiyama, H. Kakiuchi, K. Yasutake, K. Yoshii, K. Endo and Y. Mori: Extremely High-Rate Deposition of Silicon Thin Films Prepared by Atmospheric Plasma CVD Method with a Rotary Electrode, 3rd World Conference and Exhibition on Photovoltaic Solar Energy Conversion, Japan
20. T. Iwamoto, T. Ogura, M. Terai, H. Watanabe, H. Watanabe, N. Ikarashi, M. Miyamura, T. Tatsumi, M. Saitoh, A. Morioka, K. Watanabe, Y. Saito, Y. Yabe, T. Ikarashi, K. Masuzaki, Y. Mochizumi, and T. Mogami: A Highly Manufacturable Low Power and High Speed HfSiO CMOS FET with Dual Poly-Si Gate Electrodes, Tech. Digest Int. Electron Devices Meeting 2003, USA
21. A. Morioka, H. Watanabe, M. Miyamura, T. Tatsumi, M. Saito, T. Ogura, T. Iwamoto, T. Ikarashi, Y. Saito, Y. Okada, H. Watanabe, Y. Mochizuki, T. Mogami: High Mobility MISFET with Low Trapped Charge in HfSiO Films, Tech. Digest Symposium on VLSI Technology 2003, Japan

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1. K. Yasutake, H. Watanabe, H. Ohmi, H. Kakiuchi, S. Koyama, D. Nakajima and K. Minami: Formation of Crystalline Ge Islands on Glass Substrates for Growth of Large-Grained Polycrystalline Si Thin

Films, Thin Film Materials & Devices Meeting, Japan

2. S. Morita, T. Takegawa, T. Hirokane, S. Urabe, K. Arima, J. Uchikoashi and M. Morita: Nano-Gap Device for Liquid Sensing, 2004 International Conference on Solid State Devices and Materials, Japan
3. S. Morita, A. Shinozaki, Y. Morita, K. Nishimura, T. Okazaki, S. Urabe and M. Morita: Tunneling Current through Ultrathin Silicon Dioxide Films under Light Exposure, 2004 International Workshop on DIELECTRIC THIN FILMS FOR FUTURE ULSI DEVICES-SCIENCE AND TECHNOLOGY, Japan
4. K. Arima, J. Katoh and K. Endo: Hydrogen Termination of the Si(110) Surface by Wet Cleaning Revealed by Atomically Resolved Scanning Tunneling Microscopy, 2005 MRS Spring Meeting, San Francisco, USA
5. Y. Oshikane, A. Nagao, S. Sato, K. Yamamura, K. Endo: Investigation of the Role of Plasma Conditions on the Etching Performance of Silicon Wafer in the Plasma CVM Process, International COE Forum on Plasma Science and Technology, Japan
6. Y. Oshikane, A. Nagao, K. Yamamura, A. Oda, K. Endo: Fluorine and Oxygen Density Monitoring in Plasma CVM Process by Argon Actinometry Technique, 7th Asia Pacific Conference on Plasma Science and Technology and 17th Symposium on Plasma Science for Materials, Japan
7. Y. Oshikane, A. Nagao, K. Yamamura, A. Oda, K. Endo: Fluorine and Oxygen Monitoring in Plasma CVM Etching Process for Silicon Wafer by Argon Actinometry Technique, 57th Annual Gaseous Electronics Conference, Ireland
8. Y. Kuwahara, M. Akai-Kasaya, K. Takami, A. Saito and M. Aono: Electronic Properties and Electrical Conductance of Organic Molecules Swiss-Japan, Nanoscience Workshop, Japan
9. T. Uemura, M. Aono, Y. Kuwahara: Tunneling-current-induced light emission from individual carbon nanotubes, 8th International Conference on Nanometer-Scale Science and Technology, Italy
10. A. Saito, S. Yoshioka, and S. Kinoshita: Reproduction of the Morpho butterfly's blue: arbitration of contradicting factors., The SPIE 49th Annual Meeting, (Session 5526B :Stray Light Optical Systems: Analysis, Measurement, and Suppression) , USA
11. M. Akai-Kasaya, Y. Yamamoto, Y. Higuchi, A. Saito, M. Aono, Y. Kuwahara: Polaron Injection into One-dimensional Polydiacetylene Nanowire Using a Scanning Tunneling Microscope, 8th International Conference on Nanometer-Scale Science and Technology, Italy
12. Y. Kuwahara, M. Akai-Kasaya, K. Takami, A. Saito and M. Aono: The Electronic Configurations and the Electrical Conductance of Organic Molecules, SANKEN International Symposium on Scientific and Industrial Nanotechnology 2004, Japan
13. Y. Mori, K. Yamamura, K. Endo, K. Yamauchi, K. Yasutake, H. Goto, H. Kakiuchi, Y. Sano, H. Mimura: Creation of perfect surfaces, The 14th international conference on crystal growth, Switzerland
14. K. Yamauchi, K. Yamamura, H. Mimura, Y. Sano, S. Matsuyama, H. Yumoto, K. Ueno, M. Shibahara, K. Endo, M. Yabashi, K. Tamasaku, Y. Nishino, T. Ishikawa and Y. Mori: Fabrication technology of ultraprecise mirror optics to realize hard X-ray nanobeam, SPIE International Symposium, Optical Science and Technology, SPIE, USA
15. H. Mimura, H. Yumoto, K. Yamamura, Y. Sano, S. Matsuyama, K. Ueno, K. Endo, Y. Mori, M. Yabashi,

- K. Tamasaku, Y. Nishino, T. Ishikawa and K. Yamauchi: Microstitching Interferometry for hard X-ray nanofocusing mirrors, SPIE, USA
16. S. Matsuyama, H. Mimura, K. Yamamura, H. Yumoto, Y. Sano, K. Endo, Y. Mori, M. Yabashi, K. Tamasaku, Y. Nishino, T. Ishikawa and K. Yamauchi: Wave-optical and ray-tracing analysis to establish a two dimensional focusing unit using K-B arrangement, SPIE, USA
 17. K. Yamauchi, K. Yamamura, H. Mimura, Y. Sano, S. Matsuyama, H. Yumoto, K. Ueno, K. Endo, M. Yabashi, K. Tamasaku, Y. Nishino, T. Ishikawa and Y. Mori: Surface Figure Metrology of x-ray mirrors using optical interferometry, Production Metrology for Precision Surface, Germany
 18. H. Mimura, K. Yamauchi: Development of surface figuring and smoothing technologies for ultraprecise X-ray mirror fabrication at Osaka university., The 9th SPring-8, ESRF, APS Workshop, Japan
 19. H. Mimura, K. Yamauchi: Development of hard X-ray nanofocusing system using ultraprecisely figured mirrors at SPring-8, The 9th SPring-8, ESRF, APS Workshop, Japan
 20. Y. Ichii, K. Yagi, T. Ono, H. Goto, K. Inagaki, K. Yamauchi, K. Endo, Y. Mori and K. Hirose: First-Principles Molecular-Dynamics Simulations of Electrochemical Etching Process on Al(001) Cathode Surface, The 7th Asian Workshop on First-Principles Electronic Structure Calculations, Taiwan
 21. K. Yagi, Y. Ichii, T. Ono, H. Goto, K. Inagaki, K. Yamauchi, K. Endo, Y. Mori and K. Hirose: First-Principles Molecular-Dynamics Simulations of Dissociation Process of Water Molecule by Catalytic Reaction of Ion-Exchange Group, The 7th Asian Workshop on First-Principles Electronic Structure Calculations, Taiwan
 22. K. Yamuchi, H. Mimura, K. Yamamura, Y. Sano, K. Ueno, S. Matsuyama, K. Endo, Y. Nishino, K. Tamasaku, M. Yabashi, T. Ishikawa: Fabrication of ultraprecisely figured and ultrasmooth elliptical mirrors for hard X-ray nanofocusing, 2nd International Symposium on Technologies and Applications of Photoelectron Micro-Spectroscopy with Laser-based VUV Sources, Japan
 23. H. Mimura, H. Yumoto, S. Matsuyama, K. Yamamura, Y. Sano, K. Endo, Y. Mori, Y. Nishino, K. Tamasaku, M. Yabashi, T. Ishikawa and K. Yamauchi: Development of surface figuring and smoothing technologies for ultraprecise X-ray mirror Fabrication, 2nd International Symposium on Technologies and Applications of Photoelectron Micro-Spectroscopy with Laser-based VUV Sources, Japan
 24. T. Sasaki, T. Ono and K. Hirose: First-Principles Calculation Method For Electronic Structures Of Nanostructures Intervening Between Semi-Infinite Electrodes, TNT 2004 Trends in Nanotechnology, Spain
 25. Y. Egami, T. Ono and K. Hirose: First-Principles Study On Conduction Properties Of Nanostructure, TNT 2004 Trends in Nanotechnology, Spain
 26. T. Ono and K. Hirose: First-Principles Study On Electron Transport Property Through Nanostructures, TNT 2004 Trends in Nanotechnology, Spain
 27. Y. Egami, T. Sasaki, T. Ono and K. Hirose: First-principles study on the origin of the conductance oscillation of the single-row gold nanowire, The 7th Asian Workshop on First-Principles Electronic Structure Calculations, Taiwan

28. T. Ono, S. Horie, K. Endo and K. Hirose: Analysis of Scanning Tunneling Microscopy Image of H-Adsorbed Si(001) by First-Principles Electron-Transport Calculation, The 7th Asian Workshop on First-Principles Electronic Structure Calculations, Taiwan
29. T. Sasaki, Y. Egami, T. Ono, and K. Hirose: First-principles Calculation Method for Electronic Structures of Nanojunctions Suspended between Crystalline Electrodes, The 7th Asian Workshop on First-Principles Electronic Structure Calculations, Taiwan
30. T. Ono and K. Hirose: First-Principles Study on Electron Transport through Nanoscale Structures, XII INTERNATIONAL WORKSHOP ON COMPUTATIONAL PHYSICS AND MATERIALS SCIENCE: TOTAL ENERGY AND FORCE METHODS, Italia
31. K. Takahashi, K. Manabe, A. Morioka, T. Ikarashi, T. Yoshihara, H. Watanabe, and T. Tatsumi: High Mobility Dual Metal Gate MOS Transistors with High-k Gate Dielectrics, International Conference on Solid State Devices and Materials, Japan
32. K. Manabe, K. Takahashi, A. Morioka, H. Watanabe, T. Yoshihara, and T. Tatsumi: Fully Silicided NiSi Gates on HfSiON Gate Dielectrics for Low Power Application, International Conference on Solid State Devices and Materials, Japan
33. M. Saitoh, N. Ikarashi, H. Watanabe, S. Fujieda, H. Watanabe, T. Iwamoto, A. Morioka, T. Ogura, M. Terao, K. Watanabe, M. Miyamura, T. Tatumai, T. Ikarashi, K. Masuzaki, Y. Saito, and Y. Yabe: 1.2nm HfSiON/SiON Stacked Gate Insulators for 65nm-node MISFETs International, Conference on Solid State Devices and Materials, Japan
34. Y. Yasuda, N. Kimizuka, T. Iwamoto, S. Fujieda, T. Ogura, H. Watanabe, T. Tatsumi, I. Yamamoto, K. Ito, H. Watanabe, Y. Yamagata and K. Imai: A 65nm-node LSTP (Low Standby Power) Poly-Si/a-Si/HfSiON Transistor with High Ion-Istandby Ratio and Reliability, Technology Digest Symposium on VLSI Technology, USA
35. M. Miyamura, M. Masuzaki, H. Watanabe, N. Ikarashi, and T. Tatsumi: Origin of Flatband Voltage Shift in Poly-Si/Hf-based High-k Gate Dielectrics and V_{fb} Dependence on Gate Stack Structure, International Workshop on Dielectric Thin Films for Future ULIS Devices - Science and Technology, Japan
36. K. Tatsumura, T. Watanabe, I. Ohdomari, T. Chikyow, T. Shimura, M. Umeno: Residual Order within Thermally Grown SiO_2 on Si(113) Substrate, International Workshop on Dielectric Thin Films for Future ULIS Devices - Science and Technology, Japan
37. H. Watanabe, M. Saitoh, N. Ikarashi, and T. Tatsumi: High Quality HfSi_xO_y Gate Dielectrics Fabricated by Solid Phase Reaction Between Metal Hf and SiO_2 Underlayer, Material Research Society Spring Meeting, USA
38. N. Umezawa, K. Shiraishi, T. Ohno, H. Watanabe, T. Chikow, K. Torii, K. Yamabe, K. Yamada, H. Kitajima, and T. Arikado: Intrinsic Effects of a Nitrogen Atom for Reduction in Leakage Current through Hf-based High-k Gate Dielectrics -Nitrogen Induced Atomistic Cutoff of O Vacancy Mediated Leakage Paths-, 35th IEEE Semiconductor Interface Specialists Conference, USA
39. K. Takahashi, K. Manabe, T. Ikarashi, N. Ikarashi, T. Hase, T. Yoshihara, H. Watanabe, T. Tatsumi, and Y. Mochizuki: Dual Workfunction Ni-Silicide/HfSiON Gate Stacks by Phase-Controlled

Full-Silicidation (PC-FUSI) Technique for 45nm-node LSTP and LOP Devices, Technical Digest of International Electron Devices Meeting, USA

40. T. Shimura, E. Mishima, K. Fukuda, K. Yasutake, and M. Umeno: Development of Characterization Technique of SOI Wafers by Synchrotron X-ray Topography, 4th International Symposium on Advanced Science and Technology of Silicon Materials, USA
41. K. Yamamura, Y. Mori, Y. Sano: Machining of next generation semiconductor materials by plasma chemical vaporization machining, 14th international conference on crystal growth, France

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1. H. Ohmi, H. Kakiuchi, Y. Ogiyama, H. Watanabe, K. Yasutake: Characterization of high pressure (200-760Torr), stable glow plasma of pure hydrogen by measuring etching properties of Si and optical emission spectroscopy, 6th International Conference on Reactive Plasmas and 23rd Symposium on Plasma Processing, Japan
2. H. Kakiuchi, H. Ohmi, R. Nakamura, M. Aketa, K. Yasutake, K. Yoshii, Y. Mori: Deposition Characteristics of Polycrystalline Silicon Carbide Films Prepared at High-Rates by Atmospheric Pressure Plasma CVD, 6th International Conference on Reactive Plasmas and 23rd Symposium on Plasma Processing, Japan
3. H. Ohmi, H. Kakiuchi, N. Tawara, T. Wakamiya, T. Shimura, H. Watanabe, K. Yasutake: Low-temperature Growth of Epitaxial Silicon films by Atmospheric Pressure Plasma Chemical Vapor Deposition, 6th International Conference on Reactive Plasmas and 23rd Symposium on Plasma Processing, Japan
4. H. Ohmi, H. Kakiuchi, K. Nishijima, H. Watanabe, K. Yasutake: low temperature crystallization of amorphous silicon by atmospheric pressure plasma treatment in H₂/He or H₂/Ar mixtures, 6th International Conference on Reactive Plasmas and 23rd Symposium on Plasma Processing, Japan
5. H. Kakiuchi, H. Ohmi, Y. Kuwahara, M. Matsumoto, Y. Ebata, K. Yasutake, K. Yoshii and Y. Mori: High-Rate Deposition of Intrinsic Amorphous Silicon Layers for Solar Cells using Very High Frequency Plasma at Atmospheric Pressure, 2005 International Conference on Solid State Devices and Materials, Japan
6. T. Wakamiya, H. Ohmi, H. Kakiuchi, H. Watanabe, K. Yasutake, K. Yoshii, and Y. Mori: High-Rate Growth of Defect-Free Epitaxial Si at Low Temperatures by Atmospheric Pressure Plasma CVD, 2005 International Conference on Solid State Devices and Materials, Japan
7. H. Ohmi, H. Kakiuchi, K. Yasutake, Y. Nakahama, Y. Ebata, K. Yoshii and Y. Mori: Influence of H₂/SiH₄ ratio on the deposition rate and morphology of polycrystalline silicon films deposited by atmospheric pressure plasma, CVD SOLID STATE DEVICES AND MATERIALS, Japan
8. Y. Hamaoka, H. Ohmi, H. Kakiuchi and K. Yasutake: Study of Effects of Metal layer on hydrogen desorption from hydrogenated amorphous silicon using temperature programmed desorption, SOLID STATE DEVICES AND MATERIALS, Japan
9. K. Hashimoto, Y. Ochi, T. Hirokane, S. Kawakami, S. Uchiyama, K. Fukui, K. Arima, J. Uchikoshi and

- M. Morita: Current-Voltage Characteristics of Gap Electrodes with λ DNA Molecules after Elongating Treatment, Handai Nanoscience and Nanotechnology International Symposium, Suita, 2006, Japan
10. T. Hirokane, S. Morita, T. Takegawa, S. Urabe, K. Arima, J. Uchikoshi and M. Morita: Development of Characterization Methods of Biomolecules by Semiconductor Devices, Handai Nanoscience and Nanotechnology International Symposium, Suita, 2006, Japan
 11. K. Hiwa, R. Nakaoka, M. Morita and K. Arima: Development of Surface Hall Potentiometry to Characterize Semiconductor Films, Handai Nanoscience and Nanotechnology International Symposium, pp. 91-92 (2006) , Japan
 12. N. Yoshii, T. Hirokane, S. Urabe, K. Nishimura, S. Morita, and M. Morita: CHARACTERIZATION OF TUNNELING CURRENT THROUGH ULTRATHIN SILICON DIOXIDE FILMS BY DIFFERENT-METAL GATES METHOD, ECS Transactions, USA
 13. M. Chikamoto, H. Hashimoto, K. Horikoshi, A. Shinozaki, S. Morita, K. Arima, J. Uchikoshi, and M. Morita: PHOTODETECTION CHARACTERISTICS OF SnO₂-ULTRATHIN SiO₂-Si STRUCTURES, ECS Transactions, USA
 14. S. Urabe, K. Nishimura, S. Nishikawa, S. Morita, and M. Morita: QUANTITATIVE ANALYSIS OF REACTION OF HYDROGEN-TERMINATED Si(100) WITH OXYGEN DURING HEATING, ECS Transactions, USA
 15. S. Morita, T. Hirokane, T. Takegawa, S. Urabe, K. Arima, J. Uchikoshi and M. Morita: Development of Nano-Gap Device for Biosensor, 2005 International Conference on Solid State Devices and Materials, Japan
 16. M. Chikamoto, H. Hashimoto, K. Horikoshi, A. Shinozaki, S. Morita, K. Arima, J. Uchikoshi, and M. Morita: Photodetector Characteristics of Metal-Oxide-Semiconductor Tunneling Structures with Transparent Conductive Tin Oxide Gate, 2005 International Conference on Solid State Devices and Materials, Japan
 17. K. Arima, K. Hiwa, R. Nakaoka and M. Morita: Surface Hall Potentiometry to Characterize Functional Semiconductor Films, 2005 International Conference on Solid State Devices and Materials, Japan
 18. K. Arima, T. Shigetoshi, H. Kakiuchi and M. Morita: Surface photovoltage measurements of amorphous Si films on Si wafers by STM/STS, 23rd International Conference on Defects in Semiconductors, Japan
 19. S. Nishikawa, H. Hashimoto, M. Chikamoto, M. Aoki, K. Arima, and M. Morita: Electrical Properties of SiC/p-Si(100) Structure, Fourth International Conference on Silicon Epitaxy and Heterostructures, Japan
 20. K. Arima, J. Katoh and K. Endo: Atomic Images of H-Terminated Si(110)-(1x1) Surfaces by Wet Cleaning, 13th International Conference on Scanning Tunneling Microscopy/Spectroscopy and Related Techniques, Japan
 21. K. Arima, K. Yamauchi, H. Mimura, A. Kubota, K. Inagaki, Y. Mori and K. Endo: Atomic-Scale Evaluation of Si(001) Surfaces Finished by Novel Global Planarization Process, 13th International Conference on Scanning Tunneling Microscopy/Spectroscopy and Related Techniques, Japan
 22. K. Arima and K. Endo: Atomic-scale Control of Semiconductor Surfaces in Aqueous Environment for

Nano-scale Devices, Handai Nanoscience and Nanotechnology International Symposium, Japan

23. J. Uchikoshi, A. Tsuda, N. Ajari, T. Okamoto, A. Funamoto, K. Arima, and M. Morita: Nano-Flatness Measurements of Silicon Mirrors by Near-Infrared Ray Interferometry, Handai Nanoscience and Nanotechnology International Symposium, Japan
24. K. Arima, K. Yamauchi, H. Mimura, A. Kubota, K. Inagaki, Y. Mori, and K. Endo: Atomic-level STM analyses of Si(001) surfaces prepared in aqueous environment, 33rd Conference on the Physics & Chemistry of Semiconductor Interfaces, USA
25. Y. Oshikane, A. Nagao, A. Oda, C. M. Western, K. Yamamura, K. Endo: Two-dimensional Actinometric Study of Fluorine and Oxygen Atom Densities in the CVM Plasma Gap and the Temperature Estimation with Electronic Spectra of Diatomic Molecules, 17th International Symposium on Plasma Chemistry, Canada
26. A. Saito, J. Maruyama, K. Manabe, K. Kitamoto, K. Tkahashi, K. Takami, S. Hirotsune, Y. Tanaka, M. Yabashi, M. Ishii, M. Akai-Kasaya, S. Shin, T. Ishikawa, Y. Kuwahara, M. Aono: Scanning Tunneling Microscope Combined with Hard X-ray Micro-Beam of High Brilliance from Synchrotron Radiation Source, 13th International Conference on Scanning Tunneling Microscopy/Spectroscopy and Related Techniques (STM'05) July 3-8, 2005 Sapporo Convention Center, Japan
27. Y. Kuwahara, K. Takami, M. Akai-Kasaya, A. Saito, M. Aono: Polaron Injection into a One-dimensional Polydiacetylene Nanowire, 13th International Conference on Scanning Tunneling Microscopy/Spectroscopy and Related Techniques (STM'05) July 3-8, 2005 Sapporo Convention Center, Japan
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29. A. Saito, J. Maruyama, K. Manabe, K. Kitamoto, K. Takahashi, Y. Tanaka, M. Yabashi, M. Ishii, M. Akai-Kasaya, S. Shin, T. Ishikawa, Y. Kuwahara, M. Aono: Scanning Tunneling Microscope Assisted with Inner-Shell Excitation by Hard X-ray Micro-Beam, AVS 52nd International Symposium & Exhibition, USA
30. A. Saito, Y. Kuwahara, S. Shin, T. Ishikawa, M. Aono: Coupling of Scanning Tunneling Microscope with Hard X-ray Micro-Beam from 27m Long Undulator at SPring-8, Workshop on the Coupling of Synchrotron Radiation IR and X-rays with Tip based Scanning Probe Microscopies, France
31. Y. Higuchi, N. Ohgami, K. Yura, M. Akai-Kasaya, A. Saito, M. Aono and Y. Kuwahara: Fabrication of nanogap flat electrodes to measure electrical transport properties of molecules, International Symposium on Molecular Scale Electronics in Conjunction with 6th Molecular Scale Electronics Workshop in Japan, 5-6 December 2005 Tsukuba, Japan
32. Y. Kuwahara and A. Saito: Development of Noble Methods of Nanoscale Functional Analysis, Handai Nanoscience and Nanotechnology International Symposium January 30 - February 1 2006 Osaka, Japan
33. H. Mimura, S. Matsuyama, H. Yumoto, H. Hara, K. Yamamura, Y. Sano, K. Endo, Y. Mori, M. Yabashi,

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 35. K. Yamauchi, H. Mimura, K. Endo, Y. Mori: Elastic Emission Machining (EEM), IWCGT-3, Switzerland
 36. Y. Sano, K. Yamamura, K. Endo, Y. Mori: Plasma Chemical Vaporization Machining (PCVM), IWCGT-3, Switzerland
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